

ABSTRACT

A method for eliminating defects in single crystal silicon, which comprises subjecting single crystal silicon prepared by the CZ method to an oxidation treatment and then to an ultra high temperature heat treatment at a temperature of at least 1300°C, or comprises subjecting single crystal silicon which is prepared by the CZ method and is not subjected to an oxidation treatment (a bare wafer) to an ultra high temperature heat treatment in an oxygen atmosphere and at a temperature of higher than 1200°C and lower than 1310°C. The method allows the elimination of void defects present in single crystal silicon with reliability.